

IN THE CLAIMS:

1.-34.. (Cancelled)

35. (Currently Amended) A semiconductor light emitting device comprising:

a base substrate;

~~a multilayer epitaxial structure includes a first conductive layer, a second
conductive layer and a light emitting layer that is formed between the first conductive layer and
the second conductive layer, the multilayer epitaxial structure being formed on the base substrate
in such a manner that the first conductive layer is positioned closer to the base substrate than the
second conductive layer is;~~

~~a first electrode that is formed on the first conductive layer;~~

~~a second electrode that is formed on the second conductive layer;~~

~~an insulating film that covers side surfaces of the multilayer epitaxial structure
and separates the first electrode and the second electrode;~~

~~a first power supply terminal and a second power supply terminal that are formed
on a main surface of the base substrate which faces away from the multilayer epitaxial structure;~~

~~a first conductive member including a first through hole that is provided in the
base substrate, and electrically connecting the first electrode and the first power supply terminal;~~

~~a second conductive member including a second through hole that is provided in
the base substrate, and electrically connecting the second electrode and the second power supply
terminal; and~~

~~a phosphor film having an even thickness that covers a main surface of the
multilayer epitaxial structure.~~

a base substrate (4); and

a pair of power supply terminal thin-film layers (36, 38), each being provided on different areas of a first main surface of the base substrate, and the pair of power supply terminal thin-film layers being electrically connected to each other via through-holes (42, 46) provided in the base substrate, wherein

a second main surface of the base substrate has provided thereon a semiconductor multilayer epitaxial structure including a first conductive layer (16), a light emitting layer (14), and a second conductive layer (12) formed in the stated order,

a first electrode thin-film layer (22) is in contact with the first conductive layer,

a second electrode thin-film layer (24) is in contact with the second conductive layer,

a phosphor film covers the semiconductor multilayer epitaxial structure, and

a first thin-film layer (40) and a second thin-film layer (30) electrically connect the first electrode thin-film layer (22) and the second electrode thin-film layer (24) respectively via the through-holes.

36. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure; and

the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

37. (Previously Presented) The semiconductor light emitting device of Claim 35, further comprising:

a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

38.-39. (Cancelled)

40. (Previously Presented) The semiconductor light emitting device of Claim 35 wherein

the multilayer epitaxial structure having a structural characteristic of epitaxial growth on a single-crystal substrate different from the base substrate, is mounted on the base
5 substrate.

41. (Currently Amended) The semiconductor light emitting device of Claim 40, wherein

the multilayer epitaxial structure is mounted to the base substrate in such a manner that a last epitaxially-grown layer having grown on ~~[[a]]~~ the single-crystal substrate
5 different from the base substrate is positioned closer to the base substrate than a first epitaxially-grown layer is.

42.-45. (Cancelled)

46. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the first and the second through holes are positioned in a periphery of the base substrate, and

5 the multilayer epitaxial structure is not positioned on or over the first and second through holes.

47. (Cancelled)

48. (Previously Presented) The semiconductor light emitting device of Claim 47, wherein

the multilayer epitaxial structure is mounted on the base substrate in such a manner that a last epitaxially-grown layer having a structure characteristic of being grown on a
5 single-crystal substrate different from the base substrate is positioned closer to the base substrate than a portion of a first epitaxially-grown layer.

49. (Previously Presented) The semiconductor light emitting device of Claim 47 wherein the base substrate is a SiC substrate.

50.-51. (Cancelled)

52. (New) The semiconductor light emitting device of Claim 35, wherein
the phosphor layer covers an entirety of the base substrate, including surrounding
edge portions of the base substrate, and

a peripheral lateral surface of the base substrate and a peripheral lateral surface of
5 the phosphor layer are a continuous surface.